

LM3485/LM3485Q

Hysteretic PFET Buck Controller

General Description

The LM3485 is a high efficiency PFET switching regulator controller that can be used to quickly and easily develop a small, low cost, switching buck regulator for a wide range of applications. The hysteretic control architecture provides for simple design without any control loop stability concerns using a wide variety of external components. The PFET architecture also allows for low component count as well as ultra-low dropout, 100% duty cycle operation. Another benefit is high efficiency operation at light loads without an increase in output ripple.

Current limit protection is provided by measuring the voltage across the PFET's $R_{DS(ON)}$, thus eliminating the need for a sense resistor. The cycle-by-cycle current limit can be adjusted with a single resistor, ensuring safe operation over a range of output currents.

Features

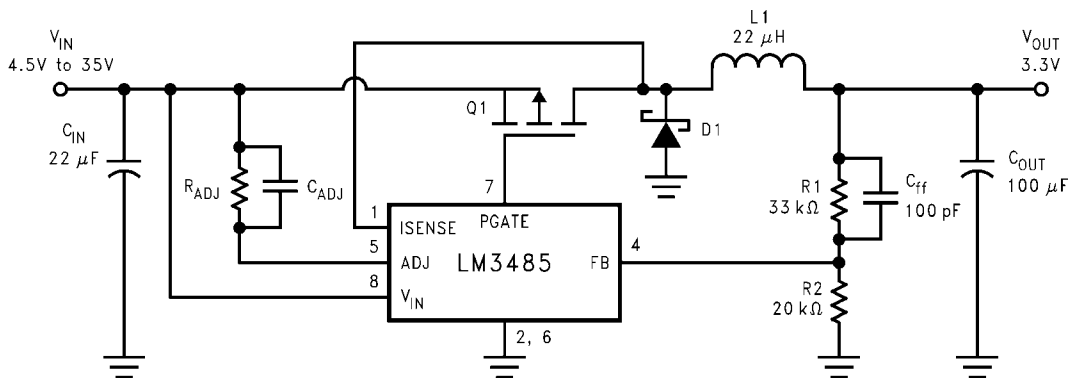
- Easy to use control methodology
- No control loop compensation required
- 4.5V to 35V wide input range

- 1.242V to V_{IN} adjustable output range
- High Efficiency 93%
- $\pm 1.3\%$ ($\pm 2\%$ over temp) internal reference
- 100% duty cycle
- Maximum operating frequency > 1MHz
- Current limit protection
- MSOP-8
- LM3485Q is AEC-Q100 Grade 1 qualified and are manufactured on an Automotive Grade Flow

Applications

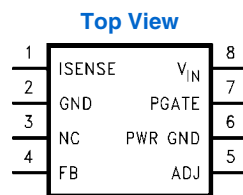
- Set-Top Box
- DSL/Cable Modem
- PC/IA
- Auto PC
- TFT Monitor
- Battery Powered Portable Applications
- Distributed Power Systems
- Always On Power

Typical Application Circuit



20034608

Connection Diagram



20034609

8 Lead Plastic MSOP-8
NS package Number MUA08A

Package Marking and Ordering Information

Order Number	Package Type	Package Marking	Supplied As	Feature
LM3485MM	MSOP-8	S29B	1000 units on Tape and Reel	AEC-Q100 Grade 1 qualified. Automotive Grade Production Flow*
LM3485MMX		S29B	3500 units on Tape and Reel	
LM3485Q1MM		SVJB	1000 units on Tape and Reel	
LM3485Q1MMX		SVJB	3500 units on Tape and Reel	

*Automotive Grade (Q) product incorporates enhanced manufacturing and support processes for the automotive market, including defect detection methodologies. Reliability qualification is compliant with the requirements and temperature grades defined in the AEC-Q100 standard. Automotive grade products are identified with the letter Q. For more information go to <http://www.national.com/automotive>.

Pin Descriptions

Pin Name	Pin Number	Description
ISENSE	1	The current sense input pin. This pin should be connected to Drain node of the external PFET.
GND	2	Signal ground.
NC	3	No connection.
FB	4	The feedback input. Connect the FB to a resistor voltage divider between the output and GND for an adjustable output voltage.
ADJ	5	Current limit threshold adjustment. It connects to an internal 5.5μA current source. A resistor is connected between this pin and the input Power Supply. The voltage across this resistor is compared with the V_{DS} of the external PFET to determine if an over-current condition has occurred.
PWR GND	6	Power ground.
PGATE	7	Gate Drive output for the external PFET. PGATE swings between V_{IN} and $V_{IN}-5V$.
VIN	8	Power supply input pin.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

VIN Voltage	−0.3V to 36V
PGATE Voltage	−0.3V to 36V
FB Voltage	−0.3V to 5V
ISENSE Voltage	−1.0V to 36V
ADJ Voltage	−0.3V to 36V
Maximum Junction Temp.	150°C
Power Dissipation	417mW @ T _A = 25°C

ESD Susceptibility
Human Body Model (Note 3)

2kV

Lead Temperature
Vapor Phase (60 sec.)
Infrared (15 sec.)

215°C

220°C

Storage Temperature

−65°C to 150°C

Operating Ratings (Note 1)

Supply Voltage	4.5V to 35V
Operating Junction Temperature	−40°C to +125°C

Electrical Characteristics

Specifications in Standard type face are for T_J = 25°C, and in **bold type face** apply over the full **Operating Temperature**

Range (T_J = −40°C to +125°C). Unless otherwise specified, V_{IN} = 12V, V_{ISNS} = V_{IN} − 1V, and V_{ADJ} = V_{IN} − 1.1V. Datasheet min/max specification limits are guaranteed by design, test, or statistical analysis.

Symbol	Parameter	Conditions	Min (Note 4)	Typ (Note 5)	Max (Note 4)	Unit
I _Q	Quiescent Current at ground pin	FB = 1.5V (Not Switching)		250	400	μA
V _{FB}	Feedback Voltage (Note 6)		1.226 1.217	1.242	1.258 1.267	V
V _{HYST}	Comparator Hysteresis			10 14	15 20	mV
V _{CL} (Note 7)	Current limit comparator trip voltage	R _{ADJ} = 20kΩ R _{ADJ} = 160kΩ		110 880		mV
V _{CL_OFFSET}	Current limit comparator offset	V _{FB} = 1.5V	−20	0	+20	mV
I _{CL_ADJ}	Current limit ADJ current source	V _{FB} = 1.5V	3.0	5.5	7.0	μA
T _{CL}	Current limit one shot off time	V _{ADJ} = 11.5V V _{ISNS} = 11.0V V _{FB} = 1.0V	6	9	14	μs
R _{PGATE}	Driver resistance	Source I _{SOURCE} = 100mA Sink I _{Sink} = 100mA		5.5 8.5		Ω
I _{PGATE}	Driver Output current	Source V _{IN} = 7V, P _{GATE} = 3.5V Sink V _{IN} = 7V, P _{GATE} = 3.5V		0.44 0.32		A
I _{FB}	FB pin Bias Current (Note 8)	V _{FB} = 1.0V		300	750	nA
T _{ONMIN_NOR}	Minimum on time in normal operation	V _{ISNS} = V _{ADJ} +0.1V C _{load} on OUT = 1000pF (Note 9)		100		ns
T _{ONMIN_CL}	Minimum on time in current limit	V _{ISNS} = V _{ADJ} +0.1V V _{FB} = 1.0V C _{load} on OUT = 1000pF (Note 9)		175		ns
%V _{FB} /ΔV _{IN}	Feedback Voltage Line Regulation	4.5 ≤ V _{IN} ≤ 35V		0.010		%/V

Note 1: Absolute maximum ratings are limits beyond which damage to the device may occur. Operating Ratings are conditions for which the device is intended to be functional, but device parameter specifications may not be guaranteed. For guaranteed specifications and test conditions, see the Electrical Characteristics.

Note 2: The maximum allowable power dissipation is a function of the maximum junction temperature, T_{J_MAX} , the junction-to-ambient thermal resistance, $\theta_{JA} = 240^{\circ}\text{C/W}$, and the ambient temperature, T_A . The maximum allowable power dissipation at any ambient temperature is calculated using:

$P_{D_MAX} = (T_{J_MAX} - T_A) / \theta_{JA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature.

Note 3: The human body model is a 100 pF capacitor discharged through a 1.5k Ω resistor into each pin.

Note 4: All limits are guaranteed at room temperature (standard type face) and at **temperature extremes (bold type face)**. All room temperature limits are 100% tested. All limits at **temperature extremes** are guaranteed via correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

Note 5: Typical numbers are at 25°C and represent the most likely norm.

Note 6: The V_{FB} is the trip voltage at the FB pin when PGATE switches from high to low.

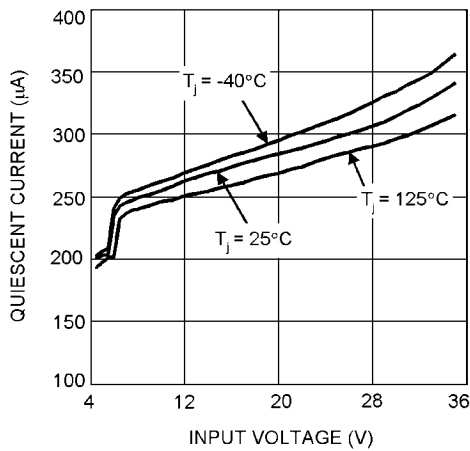
Note 7: $V_{CL} = I_{CL_ADJ} \cdot R_{ADJ}$

Note 8: Bias current flows out from the FB pin.

Note 9: A 1000pF capacitor is connected between V_{IN} and PGATE.

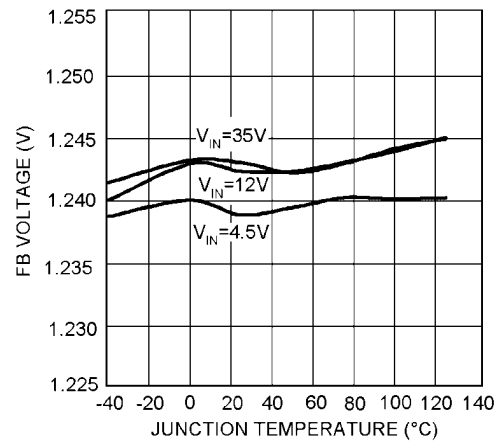
Typical Performance Characteristics Unless otherwise specified, $T_J = 25^{\circ}\text{C}$

**Quiescent Current vs Input Voltage
(FB = 1.5V)**



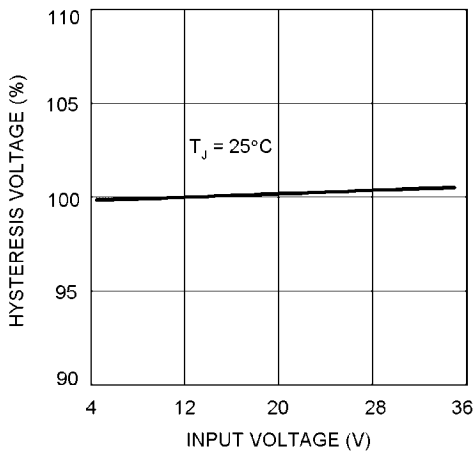
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Feedback Voltage vs Temperature



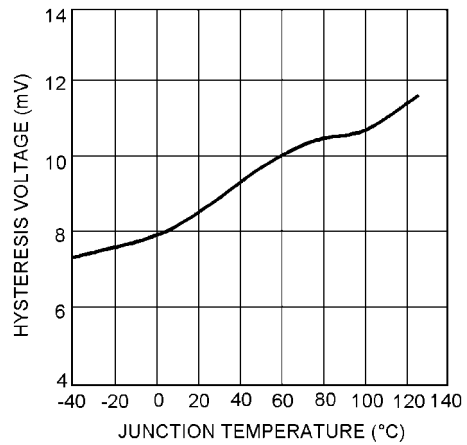
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Hysteresis Voltage vs Input Voltage



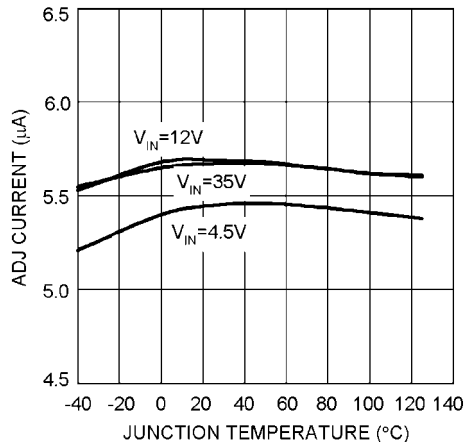
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Hysteresis Voltage vs Temperature



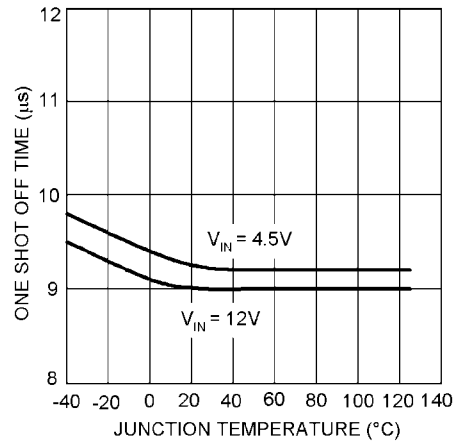
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Current Limit ADJ Current vs Temperature



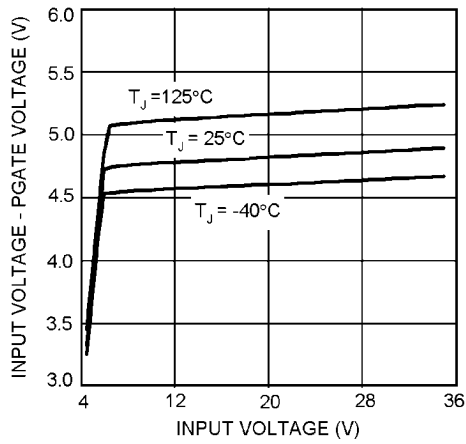
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Current Limit One Shot OFF Time vs. Temperature

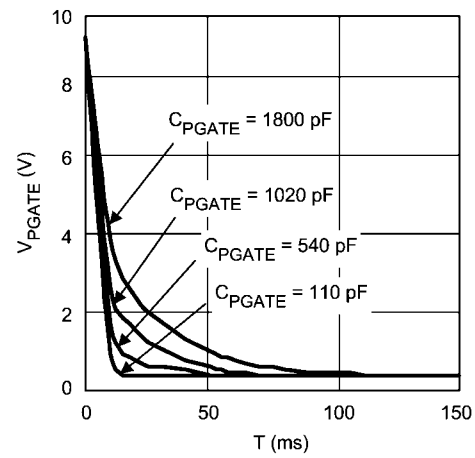


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PGATE Voltage vs Input Voltage

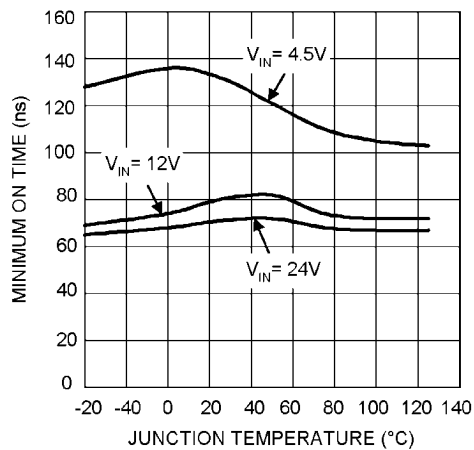


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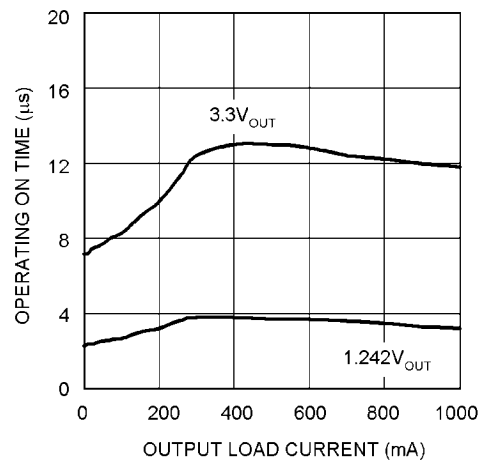
Typical V_{PGATE} vs Time
 $V_{\text{IN}} = 9\text{V}$ 

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Minimum ON Time vs. Temperature

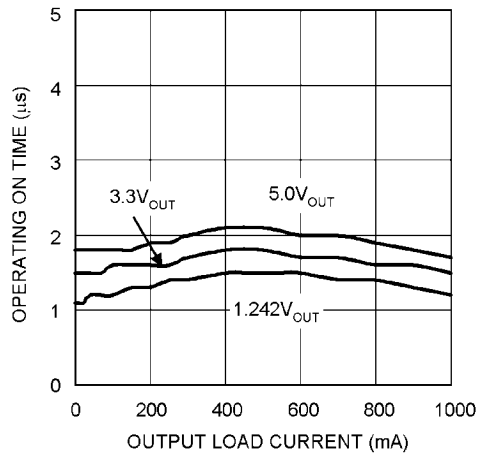


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Operating ON Time vs
Output Load Current
($V_{\text{IN}} = 4.5\text{V}$)

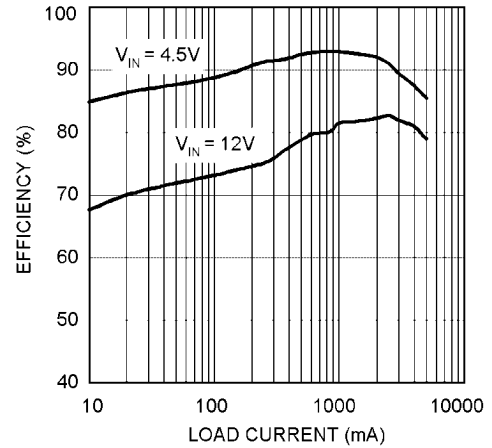
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**Operating ON Time vs
Output Load Current
($V_{IN} = 12V$)**



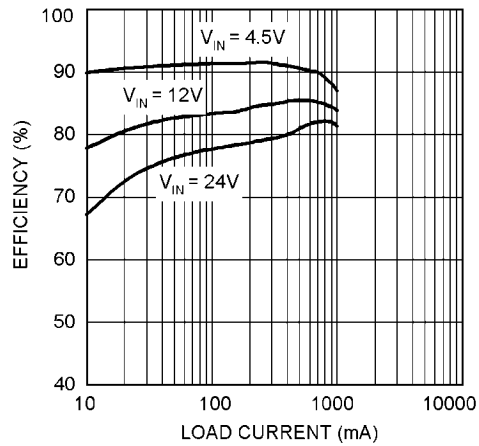
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**Efficiency vs Load Current
($V_{OUT} = 3.3V$, $L = 6.8\mu H$)**



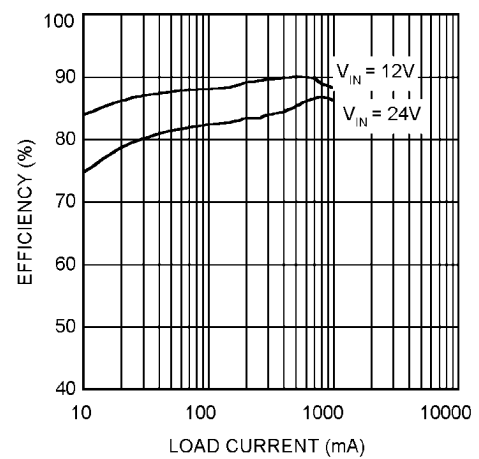
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**Efficiency vs Load Current
($V_{OUT} = 3.3V$, $L = 22\mu H$)**



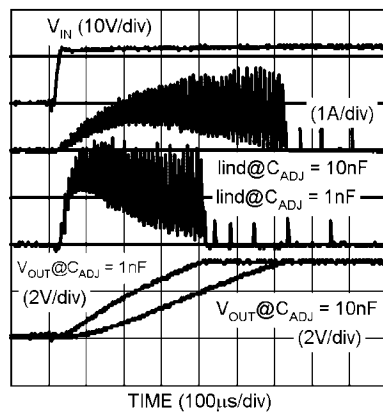
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**Efficiency vs Load Current
($V_{OUT} = 5.0V$, $L = 22\mu H$)**



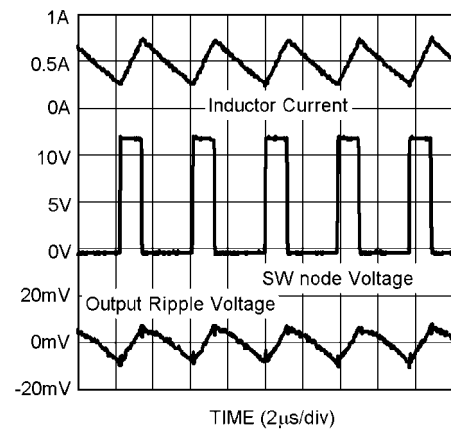
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Start Up



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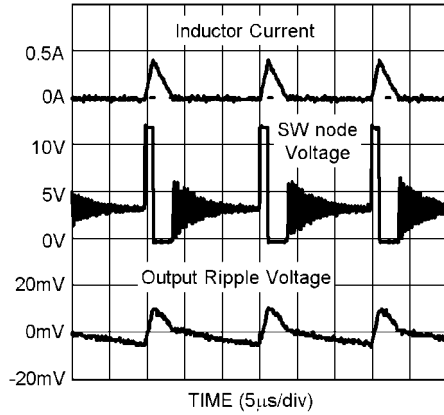
**Continuous Mode Operation
($V_{IN} = 12V$, $V_{OUT} = 3.3V$, $I_{OUT} = 500mA$, $L = 22\mu H$)**



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Discontinuous Mode Operation

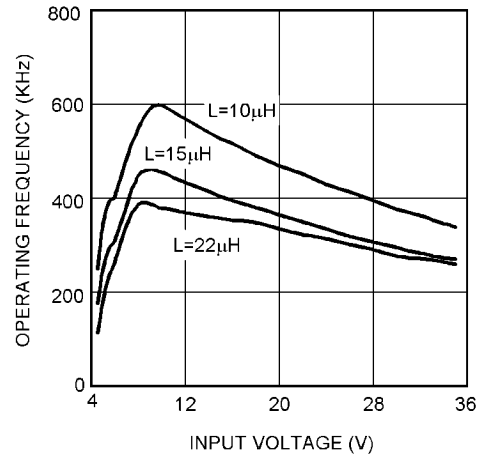
($V_{IN} = 12V$, $V_{OUT} = 3.3V$, $I_{OUT} = 50mA$, $L = 22\mu H$)



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Operating Frequency vs Input Voltage

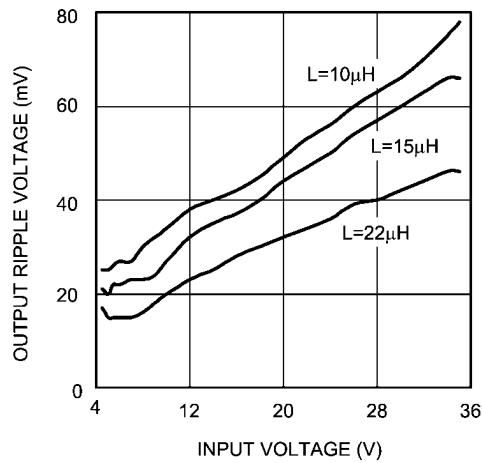
($V_{OUT} = 3.3V$, $I_{OUT} = 1A$, $C_{OUT(ESR)} = 80m\Omega$, $C_{ff} = 100pF$)



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Output Ripple Voltage vs Input Voltage

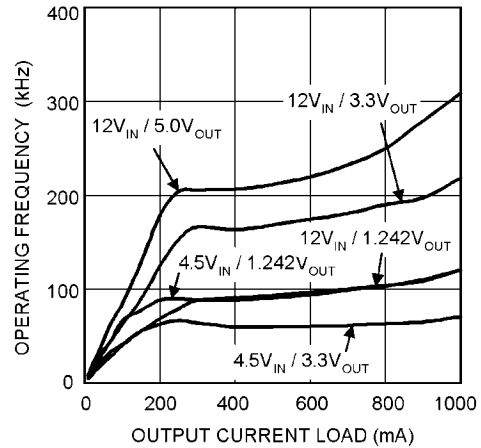
($V_{OUT} = 3.3V$, $I_{OUT} = 1A$, $C_{OUT(ESR)} = 80m\Omega$, $C_{ff} = 100pF$)



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Operating Frequency vs Output Load Current

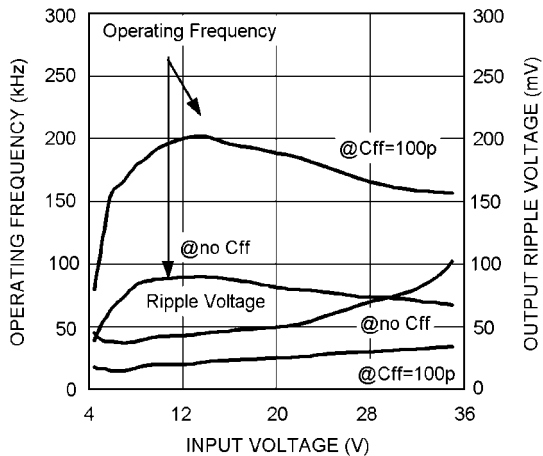
($L = 22\mu H$, $C_{OUT(ESR)} = 45m\Omega$, $C_{ff} = 100pF$)



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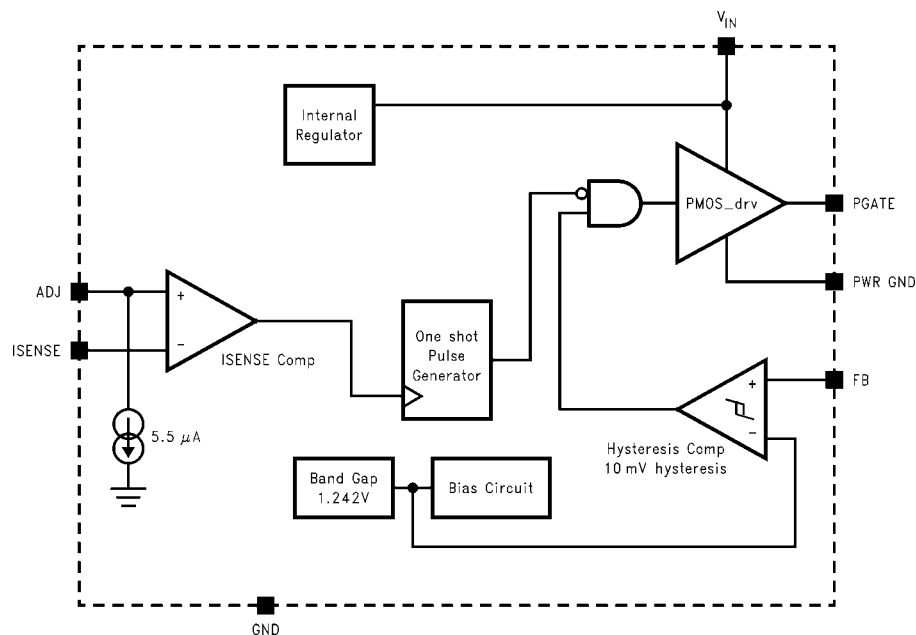
Feed-Forward Capacitor (Cff) Effect

($V_{OUT} = 3.3V$, $L = 22\mu H$, $I_{OUT} = 500mA$)



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Block Diagram



Functional Description

OVERVIEW

The LM3485 is buck (step-down) DC-DC controller that uses a hysteretic control scheme. The comparator is designed with approximately 10mV of hysteresis. In response to the voltage at the FB pin, the gate drive (PGATE pin) turns the external PFET on or off. When the inductor current is too high, the current limit protection circuit engages and turns the PFET off for approximately 9 μ s.

Hysteretic control does not require an internal oscillator. Switching frequency depends on the external components and operating conditions. Operating frequency reduces at light loads resulting in excellent efficiency compared to other architectures.

2 external resistors can easily program the output voltage. The output can be set in a wide range from 1.242V (typical) to V_{IN} .

HYSTERETIC CONTROL CIRCUIT

The LM3485 uses a comparator based voltage control loop. The feedback is compared to a 1.242V reference and a 10mV hysteresis is designed into the comparator to ensure noise free operation.

When the FB input to the comparator falls below the reference voltage, the output of the comparator moves to a low state. This results in the driver output, PGATE, pulling the gate of the PFET low and turning on the PFET. With the PFET on, the input supply charges C_{out} and supplies current to the load via the series path through the PFET and the inductor. Current through the Inductor ramps up linearly and the output voltage increases. As the FB voltage reaches the upper threshold, which is the internal reference voltage plus 10mV, the output of the comparator changes from low to high, and the PGATE responds by turning the PFET off. As the PFET turns off, the inductor voltage reverses, the catch diode turns on, and the current through the inductor ramps down. Then, as the output

voltage reaches the internal reference voltage again, the next cycle starts.

The LM3485 operates in discontinuous conduction mode at light load current or continuous conduction mode at heavy load current. In discontinuous conduction mode, current through the inductor starts at zero and ramps up to the peak, then ramps down to zero. Next cycle starts when the FB voltage reaches the internal voltage. Until then, the inductor current remains zero. Operating frequency is lower and switching losses reduce. In continuous conduction mode, current always flows through the inductor and never ramps down to zero.

The output voltage (V_{OUT}) can be programmed by 2 external resistors. It can be calculated as follows:

$$V_{OUT} = 1.242 * (R1 + R2) / R2$$

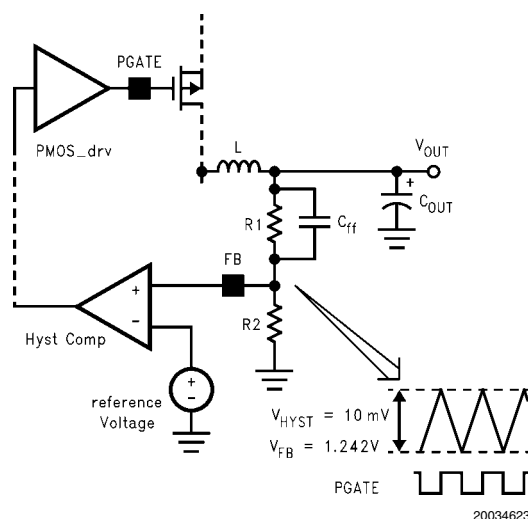


FIGURE 1. Hysteretic Window

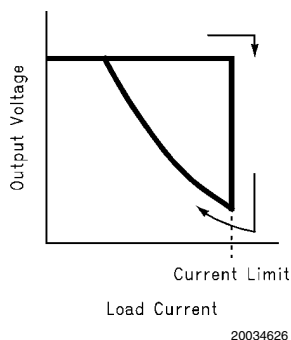


FIGURE 4. Current Limit Fold Back Phenomenon

At high input voltages (>28V) increased undershoot at the switch node can cause an increase in the current limit threshold. To avoid this problem, a low V_f Schottky catch diode must be used (See Catch Diode Selection). Additionally, a resistor can be placed between the ISENSE pin and the switch node. Any value up to approximately 600Ω is recommended.

START UP

The current limit circuit is active during start-up. During start-up the PFET will stay on until either the current limit or the feedback comparator is tripped.

If the current limit comparator is tripped first then the fold back characteristic should be taken into account. Start-up into full load may require a higher current limit set point or the load must be applied after start-up.

One problem with selecting a higher current limit is inrush current during start-up. Increasing the capacitance (C_{ADJ}) in parallel with R_{ADJ} results in soft-start. C_{ADJ} and R_{ADJ} create an RC time constant forcing current limit to activate at a lower current. The output voltage will ramp more slowly when using the soft-start functionality. There are example start-up plots for C_{ADJ} equal to 1nF and 10nF in the Typical Performance Characteristics. Lower values for C_{ADJ} will have little to no effect on soft-start.

EXTERNAL SENSE RESISTOR

The V_{DS} of a PFET will tend to vary significantly over temperature. This will result in an equivalent variation in current limit.

To improve current limit accuracy an external sense resistor can be connected from V_{IN} to the source of the PFET, as shown in Figure 5.

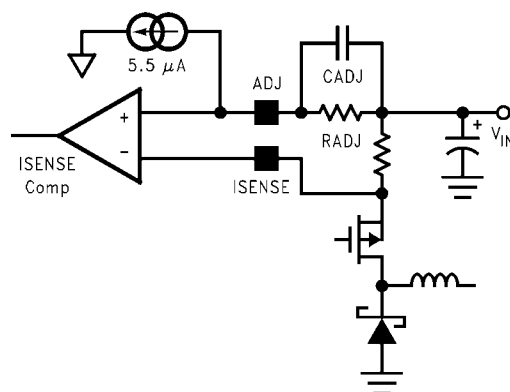


FIGURE 5. Current Sensing by External Resistor

PGATE

When switching, the PGATE pin swings from V_{IN} (off) to some voltage below V_{IN} (on). How far the PGATE will swing depends on several factors including the capacitance, on time, and input voltage.

As shown in the Typical Performance Characteristics, PGATE voltage swing will increase with decreasing gate capacitance. Although PGATE voltage will typically be around $V_{IN}-5V$, with very small gate capacitances, this value can increase to a typical maximum of $V_{IN}-8.3V$.

Additionally, PGATE swing voltage will increase as on time increases. During long on times, such as when operating at 100% duty cycle, the PGATE voltage will eventually fall to its maximum voltage of $V_{IN}-8.3V$ (typical) regardless of the PFET gate capacitance.

The PGATE voltage will not fall below 0.4V (typical). Therefore, when the input voltage falls below approximately 9V, the PGATE swing voltage range will be reduced. At an input voltage of 7V, for instance, PGATE will swing from 7V to a minimum of 0.4V.

Design Information

Hysteretic control is a simple control scheme. However the operating frequency and other performance characteristics highly depend on external conditions and components. If either the inductance, output capacitance, ESR, V_{IN} , or C_{ff} is changed, there will be a change in the operating frequency and output ripple. The best approach is to determine what operating frequency is desirable in the application and then begin with the selection of the inductor and C_{OUT} ESR.

INDUCTOR SELECTION (L1)

The important parameters for the inductor are the inductance and the current rating. The LM3485 operates over a wide frequency range and can use a wide range of inductance values. A good rule of thumb is to use the equations used for National's **Simple Switchers**®. The equation for inductor ripple (Δi) as a function of output current (I_{OUT}) is:

$$\text{for } I_{OUT} < 2.0\text{Amps}$$

$$\Delta i \leq I_{OUT} * 0.386827 * I_{OUT}^{-0.366726}$$

$$\text{for } I_{OUT} > 2.0\text{Amps}$$

$$\Delta i \leq I_{OUT} * 0.3$$

The inductance can be calculated based upon the desired operating frequency where:

$$L = \frac{V_{IN} - V_{DS} - V_{OUT}}{\Delta i} * \frac{D}{F}$$

And

$$D = \frac{V_{OUT} + V_D}{V_{IN} - V_{DS} + V_D}$$

where D is the duty cycle, V_D is the diode forward voltage, and V_{DS} is the voltage drop across the PFET.

The inductor should be rated to the following:

$$I_{pk} = (I_{OUT} + \Delta i / 2) * 1.1$$

$$I_{RMS} = \sqrt{I_{OUT}^2 + \frac{\Delta i^2}{3}}$$

The inductance value and the resulting ripple is one of the key parameters controlling operating frequency. The second is the ESR.

OUTPUT CAPACITOR SELECTION (C_{OUT})

The ESR of the output capacitor times the inductor ripple current is equal to the output ripple of the regulator. However, the V_{HYST} sets the first order value of this ripple. As ESR is increased with a given inductance, then operating frequency increases as well. If ESR is reduced then the operating frequency reduces.

The use of ceramic capacitors has become a common desire of many power supply designers. However, ceramic capacitors have a very low ESR resulting in a 90° phase shift of the output voltage ripple. This results in low operating frequency and increased output ripple. To fix this problem a low value resistor should be added in series with the ceramic output capacitor. Although counter intuitive, this combination of a ceramic capacitor and external series resistance provide highly accurate control over the output voltage ripple. The other types capacitor, such as Sanyo POS CAP and OS-

CON, Panasonic SP CAP, Nichicon "NA" series, are also recommended and may be used without additional series resistance.

For all practical purposes, any type of output capacitor may be used with proper circuit verification.

INPUT CAPACITOR SELECTION (C_{IN})

A bypass capacitor is required between the input source and ground. It must be located near the source pin of the external PFET. The input capacitor prevents large voltage transients at the input and provides the instantaneous current when the PFET turns on.

The important parameters for the input capacitor are the voltage rating and the RMS current rating. Follow the manufacturer's recommended voltage derating. For high input voltage application, low ESR electrolytic capacitor, the Nichicon "UD" series or the Panasonic "FK" series, is available. The RMS current in the input capacitor can be calculated.

$$I_{RMS_CIN} = I_{OUT} * \frac{(V_{OUT} * (V_{IN} - V_{OUT}))^{1/2}}{V_{IN}}$$

The input capacitor power dissipation can be calculated as follows.

$$P_{D(CIN)} = I_{RMS_CIN}^2 * ESR_{CIN}$$

The input capacitor must be able to handle the RMS current and the P_D . Several input capacitors may be connected in parallel to handle large RMS currents. In some cases it may be much cheaper to use multiple electrolytic capacitors than a single low ESR, high performance capacitor such as OSCON or Tantalum. The capacitance value should be selected such that the ripple voltage created by the charge and discharge of the capacitance is less than 10% of the total ripple across the capacitor.

PROGRAMMING THE CURRENT LIMIT (R_{ADJ})

The current limit is determined by connecting a resistor (R_{ADJ}) between input voltage and the ADJ pin.

$$R_{ADJ} = I_{IND_PEAK} * R_{DS(on)} / I_{CL_ADJ}$$

where:

$R_{DS(on)}$: Drain-Source ON resistance of the external PFET

I_{CL_ADJ} : 3.0µA minimum

$$I_{IND_PEAK} = I_{LOAD} + I_{RIPPLE} / 2$$

Using the minimum value for I_{CL_ADJ} (3.0µA) ensures that the current limit threshold will be set higher than the peak inductor current.

The R_{ADJ} value must be selected to ensure that the voltage at the ADJ pin does not fall below 3.5V. With this in mind, $R_{ADJ_MAX} = (V_{IN} - 3.5) / 7\mu A$. If a larger R_{ADJ} value is needed to set the desired current limit, either use a PFET with a lower $R_{DS(on)}$, or use a current sense resistor as shown in Figure 5. The current limit function can be disabled by connecting the ADJ pin to ground and ISENSE to VIN.

CATCH DIODE SELECTION (D1)

The important parameters for the catch diode are the peak current, the peak reverse voltage, and the average power dissipation. The average current through the diode can be calculated as following.

$$I_{D_AVE} = I_{OUT} * (1 - D)$$

The off state voltage across the catch diode is approximately equal to the input voltage. The peak reverse voltage rating must be greater than input voltage. In nearly all cases a Schottky diode is recommended. In low output voltage applications a low forward voltage provides improved efficiency. For high temperature applications, diode leakage current may become significant and require a higher reverse voltage rating to achieve acceptable performance.

P-CHANNEL MOSFET SELECTION (Q1)

The important parameters for the PFET are the maximum Drain-Source voltage (V_{DS}), the on resistance ($R_{DS(ON)}$), Current rating, and the input capacitance.

The voltage across the PFET when it is turned off is equal to the sum of the input voltage and the diode forward voltage. The V_{DS} must be selected to provide some margin beyond the input voltage.

PFET drain current, I_D , must be rated higher than the peak inductor current, $I_{IND-PEAK}$.

Depending on operating conditions, the PGATE voltage may fall as low as $V_{IN} - 8.3V$. Therefore, a PFET must be selected with a V_{GS} greater than the maximum PGATE swing voltage.

As input voltage decreases below 9V, PGATE swing voltage may also decrease. At 5.0V input the PGATE will swing from V_{IN} to $V_{IN} - 4.6V$. To ensure that the PFET turns on quickly and completely, a low threshold PFET should be used when the input voltage is less than 7V.

However, PFET switching losses will increase as the V_{GS} threshold decreases. Therefore, whenever possible, a high

PCB Layout

The PC board layout is very important in all switching regulator designs. Poor layout can cause switching noise into the feedback signal and general EMI problems. For minimal inductance, the wires indicated by heavy lines should be as wide and short as possible. Keep the ground pin of the input capacitor as close as possible to the anode of the diode. This path carries a large AC current. The switching node, the node with the diode cathode, inductor, and FET drain, should be kept short. This node is one of the main sources for radiated EMI since it is an AC voltage at the switching frequency. It is always good practice to use a ground plane in the design, particularly at high currents.

The two ground pins, PWR GND and GND, should be connected by as short a trace as possible; they can be connected

threshold PFET should be selected. Total power loss in the FET can be approximated using the following equation:

$$P_{Dswitch} = R_{DS(ON)} * I_{OUT}^2 * D + F * I_{OUT} * V_{IN} * (t_{on} + t_{off}) / 2$$

where:

t_{on} = FET turn on time

t_{off} = FET turn off time

A value of 10ns to 20ns is typical for t_{on} and t_{off} .

A PFET should be selected with a turn on rise time of less than 100ns. Slower rise times will degrade efficiency, can cause false current limiting, and in extreme cases may cause abnormal spiking at the PGATE pin.

The $R_{DS(ON)}$ is used in determining the current limit resistor value, R_{ADJ} . Note that the $R_{DS(ON)}$ has a positive temperature coefficient. At 100°C, the $R_{DS(ON)}$ may be as much as 150% higher than the 25°C value. This increase in $R_{DS(ON)}$ must be considered it when determining R_{ADJ} in wide temperature range applications. If the current limit is set based upon 25°C ratings, then false current limiting can occur at high temperature.

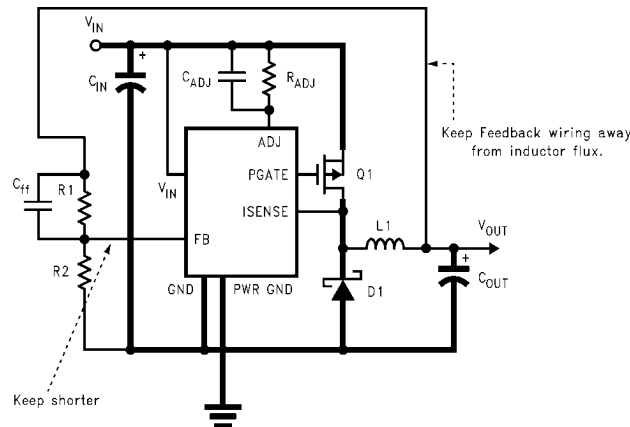
Keeping the gate capacitance below 2000pF is recommended to keep switching losses and transition times low. This will also help keep the PFET drive current low, which will improve efficiency and lower the power dissipation within the controller.

As gate capacitance increases, operating frequency should be reduced and as gate capacitance decreases operating frequency can be increased.

underneath the device. These pins are resistively connected internally by approximately 50Ω. The ground pins should be tied to the ground plane, or to a large ground trace in close proximity to both the FB divider and C_{OUT} grounds.

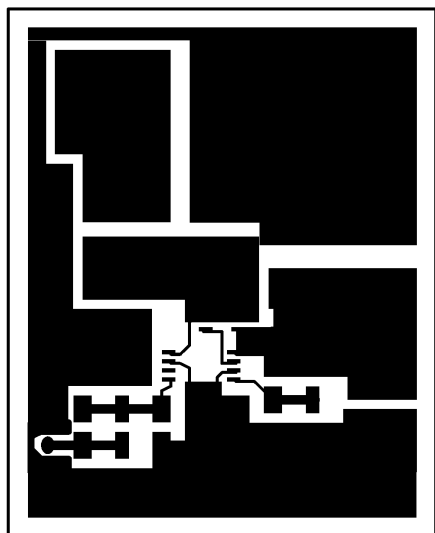
The gate pin of the external PFET should be located close to the PGATE pin. However, if a very small FET is used, a resistor may be required between PGATE and the gate of the FET to reduce high frequency ringing. Since this resistor will slow the PFET's rise time, the current limit blanking time should be taken into consideration (see Current Limit Operation).

The feedback voltage signal line can be sensitive to noise. Avoid inductive coupling to the inductor or the switching node, by keeping the FB trace away from these areas.



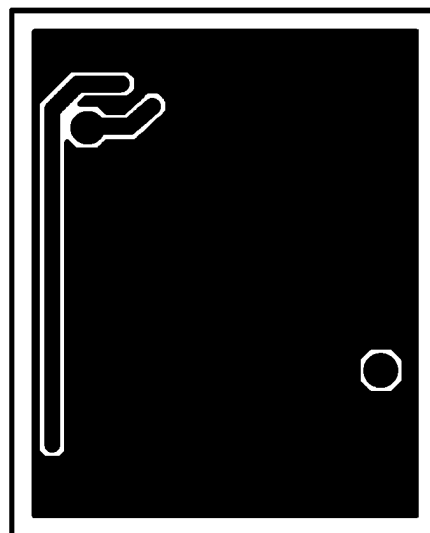
20034628

FIGURE 6. Typical PCB Layout Schematic (3.3V output)



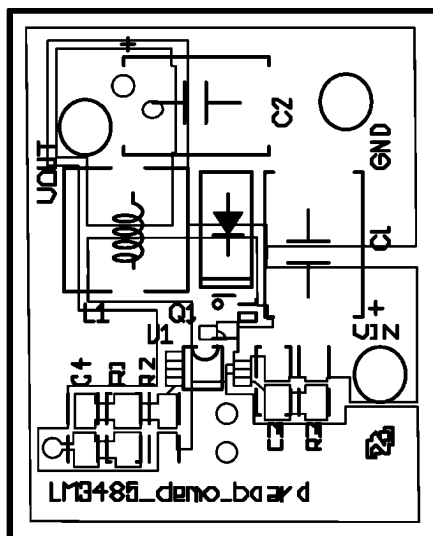
Top Layer

20034642



Bottom Layer

20034644



Silk Screen

20034641

C1: C_{IN} 22 μ F/35V EEJL1VD226R (Panasonic)

C2: C_{OUT} 100 μ F/6.3V 6TPC100M (Sanyo)

C3: C_{ADJ} 1nF Ceramic Chip Capacitor

C4: C_{FF} 100pF Ceramic Chip Capacitor

D1: 1A/40V MBRS140T3 (On Semiconductor)

L1: 22 μ H :QH66SN220M01L (Murata)

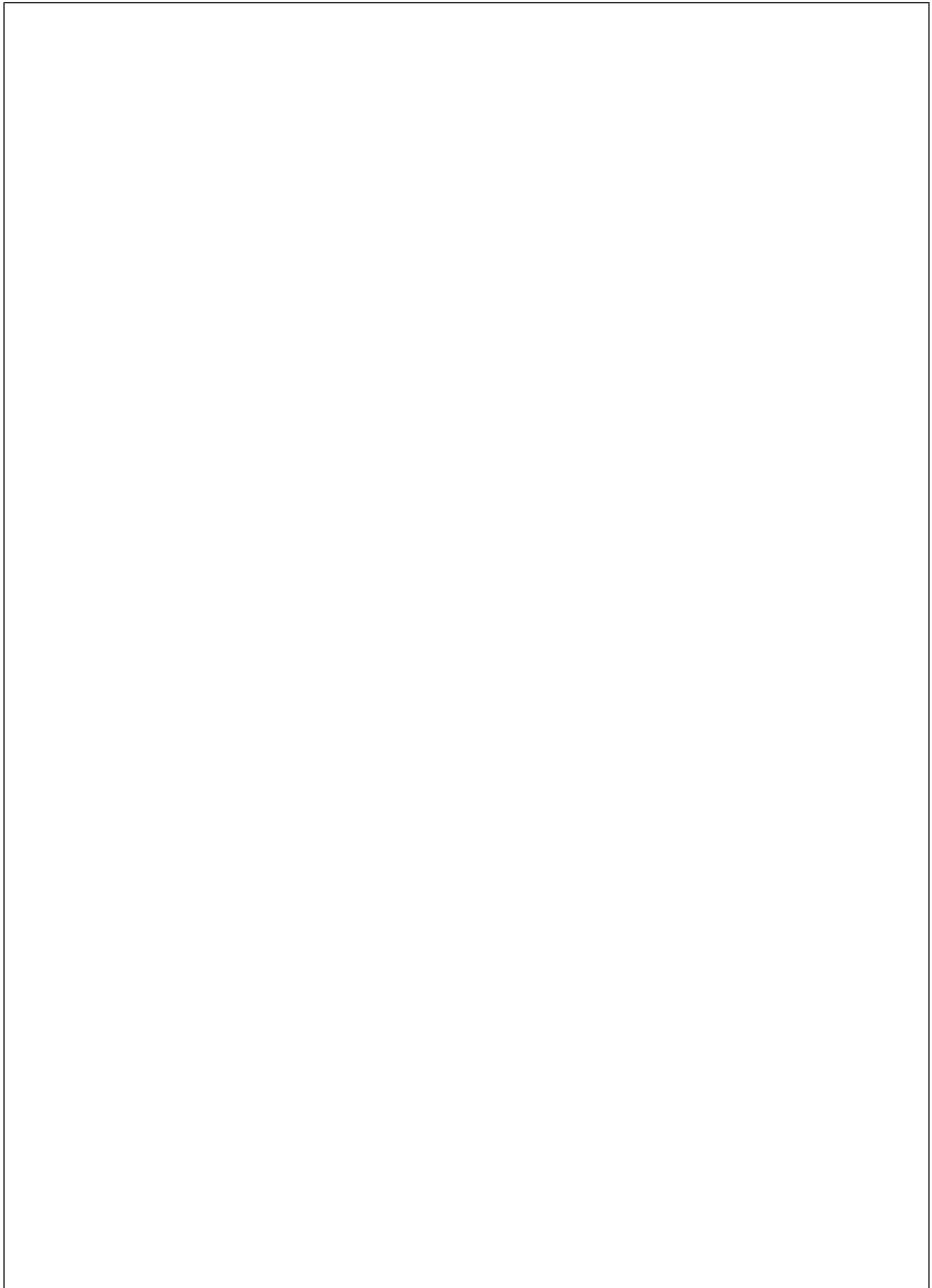
Q1: FDC5614P (Fairchild)

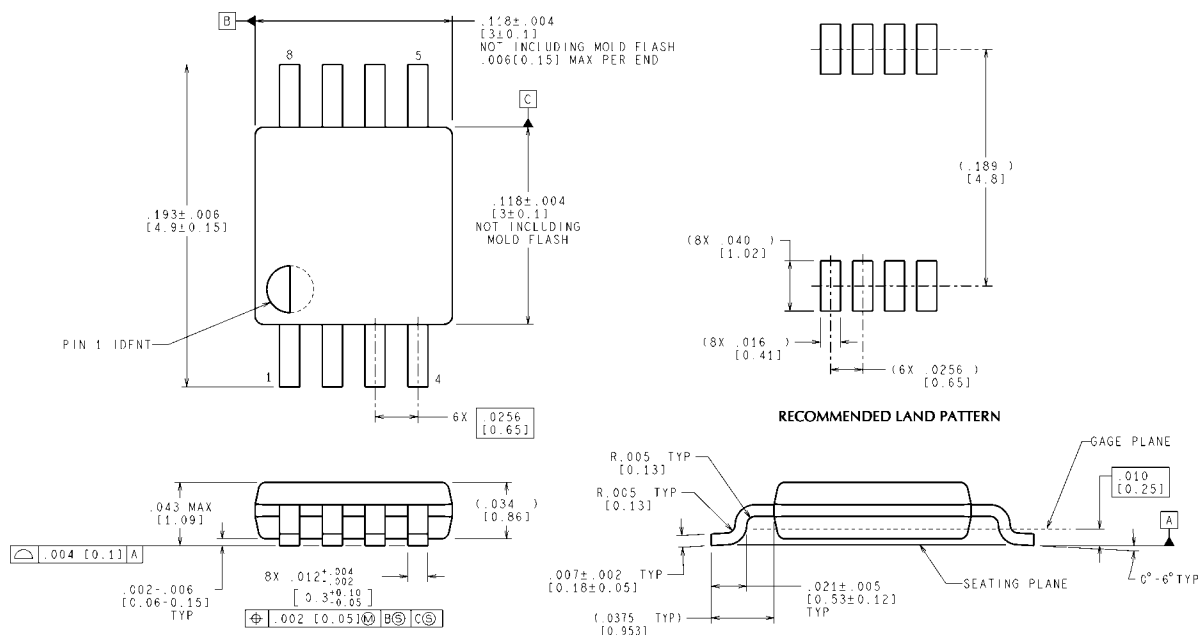
R1: 33K Ω Chip Resistor

R2: 20K Ω Chip Resistor

R3: R_{ADJ} 24K Ω Chip Resistor

FIGURE 7. Typical PCB Layout (3.3V Output)



Physical Dimensions inches (millimeters) unless otherwise noted

CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

8 Lead Plastic MSOP-8
NS package Number MUA08A

MUA08A (Rev F)

Notes

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